	Туре	Hits	Search Text	DBs	Time Stamp
1	BRS	2	6245615.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
2	BRS	2	"20010026006"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
3	BRS	2	"20020014666"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
4	BRS	2	"20020063292"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
5	BRS	2	"20020185676"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
6	BRS	59	FinFET and FET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
7	BRS	25	FinFET same FET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
8	BRS	165	Fin same FET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
9	BRS	16	Fin same FET same transistors	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 11:04
10	BRS	78	FinFET and MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
11	BRS	44	FinFET same MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
12	BRS	137	Fin same MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
13	BRS	41	Fin same MOSFET same (transistor or transistors)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 15:22

	Туре	Hits	Search Text	DBs	Time Stamp
14	BRS	14	("6770516" "6642090" "6432829" "6413802" "6252284" "6117711" "6010934").pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
15	IS&R	2	("6245615").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
16	BRS	2	"20010026006"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
17	BRS	2	"20020014666"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
18	BRS	2	"20020063292"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 15:39
19	BRS	2	"20020185676"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
20	BRS	123	FinFet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
21	BRS	5791	(etching or etched etch) near3 gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
22	BRS	84	(etching or etched etch) near3 gate adj electrode near3 top	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
23	BRS	262	(etching or etched etch) near3 gate adj electrode with (thinning or thin thined)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
24	BRS	46	(etching or etched etch) near3 gate adj electrode near3 (thinning or thin thined)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:24
25	BRS	1717	gate adj electrode with height	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 18:22
26	BRS		gate adj electrode with height and FET	· ·	2004/09/16 18:23

	Туре	Hits	Search Text	DBs	Time Stamp
27	BRS	884	gate adj electrode near3 height	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 18:23
28	BRS	244	gate adj electrode near5 height and FET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 18:23
29	BRS	73	gate adj electrode near5 height and FET and gate adj electrode near3 (etch etched etching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 18:29
30	BRS	3	("5101247" "6180499" "6333223").PN.	USPAT	2004/09/16 18:26
31	BRS	12	gate adj electrode near5 height same gate adj electrode near3 (etch etched etching) and FET		2004/09/16 18:29
32	BRS	78	gate adj electrode near5 height same gate adj electrode near3 (etch etched etching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 18:32
33	BRS	7	5858847.URPN.	USPAT	2004/09/16 18:35
34	BRS	175	438/156.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 19:37
35	BRS	703	438/258.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 19:37
36	BRS	356	438/279.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
37	BRS	536	438/286.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
38	BRS	925	438/479.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 19:37
39	BRS	191	438/517.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 19:38
40	BRS	192	438/588.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	